

CMLD4448
SURFACE MOUNT
PICOmini™
DUAL, ISOLATED
HIGH SPEED SILICON
SWITCHING DIODES



Central™

Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLD4448 type contains two (2) Isolated Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a PICOmini™ surface mount package. These devices are designed for high speed switching applications.

MARKING CODE: C48

MAXIMUM RATINGS: (T_A=25°C)

Peak Repetitive Reverse Voltage
 Continuous Forward Current
 Peak Repetitive Forward Current
 Forward Surge Current, tp=1ms
 Forward Surge Current, tp=1s
 Power Dissipation
 Operating and Storage
 Junction Temperature
 Thermal Resistance

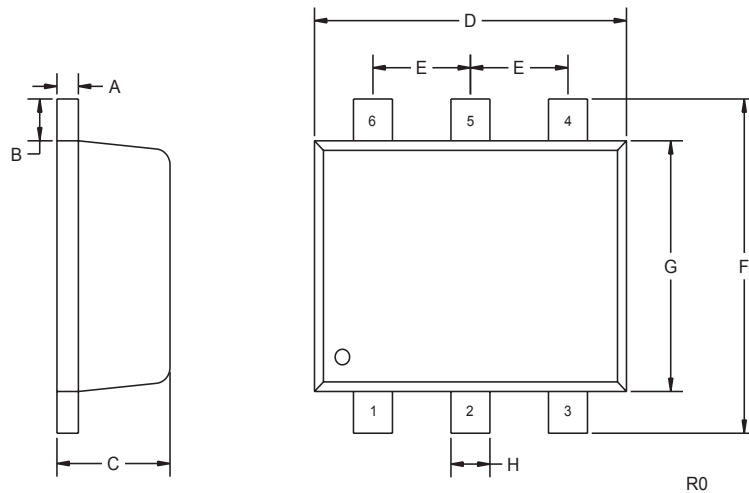
SYMBOL		UNITS
V _{RRM}	120	V
I _F	250	mA
I _{FRM}	500	mA
I _{FSM}	4.0	A
I _{FSM}	1.0	A
P _D	300	mW
T _J , T _{stg}	-65 to +150	°C
θ _{JA}	417	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
BV _R	I _R =100μA	120	150		V
I _R	V _R =50V			300	nA
I _R	V _R =50V, T _A =125°C			100	μA
I _R	V _R =100V			500	nA
V _F	I _F =1.0mA	0.55	0.59	0.65	V
V _F	I _F =10mA	0.67	0.72	0.77	V
V _F	I _F =100mA	0.85	0.91	1.0	V
C _T	V _R =0, f=1 MHz			1.5	pF
t _{rr}	I _R =I _F =10mA, R _L =100Ω, Rec. to 1.0mA		2.0	4.0	ns

R1 (2-December 2003)

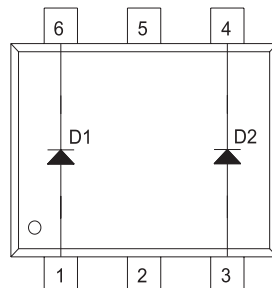
SOT-563 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.10	0.18
B	0.008		0.20	
C	0.022	0.024	0.56	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.061	0.067	1.55	1.70
G	0.047		1.20	
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R0)

Pin Configuration



LEAD CODE:

- 1) ANODE D1
- 2) NC
- 3) ANODE D2
- 4) CATHODE D2
- 5) NC
- 6) CATHODE D1

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